



BT1308 series D

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Triacs logic level

Rev. 01 — 26 February 2008

Product data sheet

1. Product profile

1.1 General description

Passivated sensitive gate triacs in a SOT54 plastic package

1.2 Features

- Sensitive gate
- Direct interfacing to logic level ICs
- Gate triggering in four quadrants
- Direct interfacing to low-power gate drive circuits

1.3 Applications

- General purpose switching and phase control
- Low-power AC fan speed control

1.4 Quick reference data

- $V_{DRM} \leq 400$ V (BT1308-400D)
- $V_{DRM} \leq 600$ V (BT1308-600D)
- $I_{TSM} \leq 9$ A ($t = 20$ ms)
- $I_{GT} \leq 5$ mA
- $I_{GT} \leq 7$ mA (T2– G+)
- $I_{T(RMS)} \leq 0.8$ A

2. Pinning information

Table 1. Pinning

| Pin | Description | Simplified outline | Graphic symbol |
|-----|----------------------|--------------------|----------------|
| 1 | main terminal 2 (T2) | SOT54 (TO-92) | sym051 |
| 2 | gate (G) | | |
| 3 | main terminal 1 (T1) | | |

3. Ordering information

Table 2. Ordering information

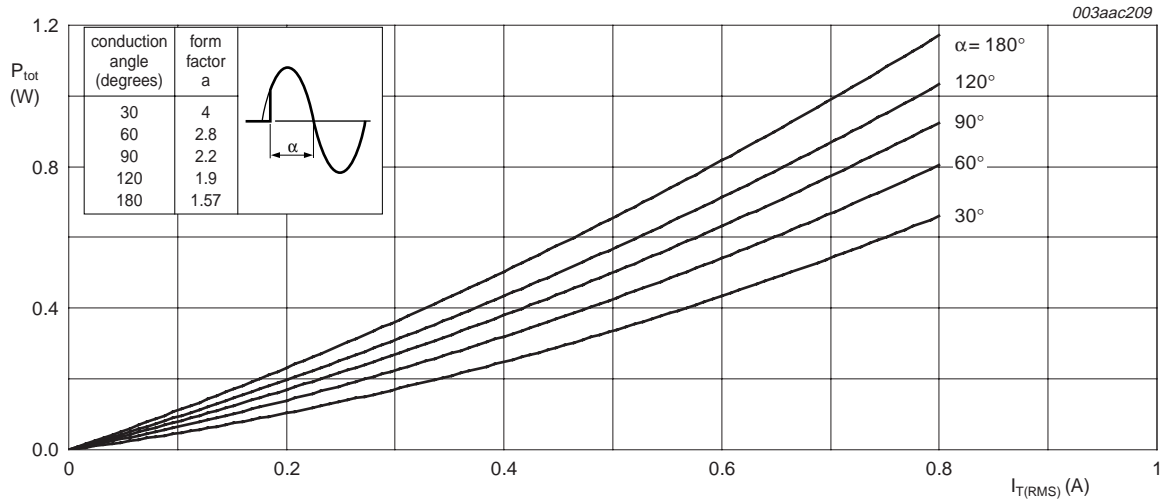
| Type number | Package | | Version |
|-------------|---------|---|---------|
| | Name | Description | |
| BT1308-400D | TO-92 | plastic single-ended leaded (through hole) package; 3 leads | SOT54 |
| BT1308-600D | | | |

4. Limiting values

Table 3. Limiting values

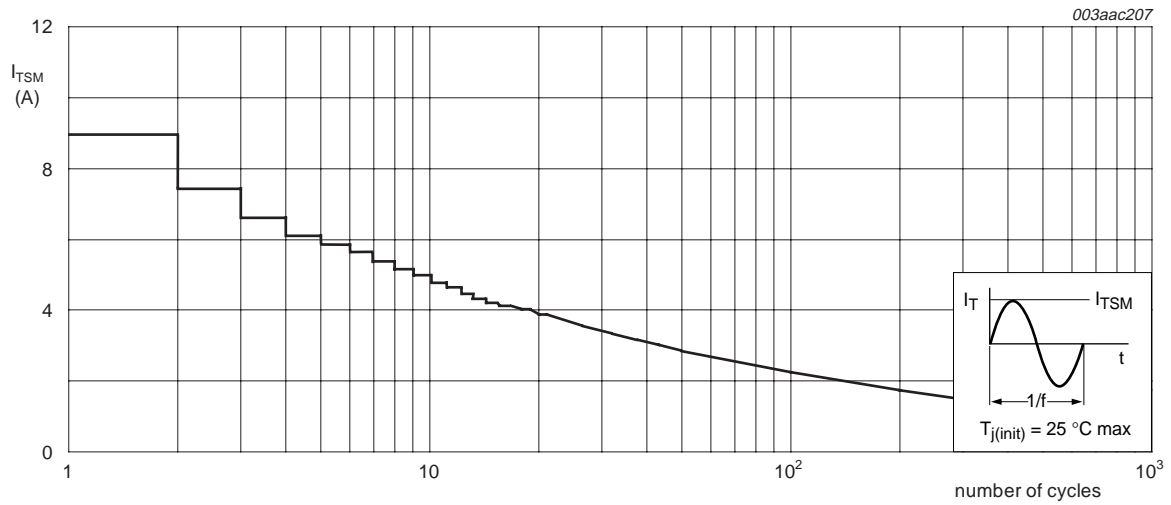
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|--------------------------------------|---|-----|------|------------------------|
| V_{DRM} | repetitive peak off-state voltage | BT1308-400D | - | 400 | V |
| | | BT1308-600D | - | 600 | V |
| $I_{\text{T(RMS)}}$ | RMS on-state current | full sine wave; $T_{\text{lead}} \leq 55\text{ °C}$; see Figure 4 and 5 | - | 0.8 | A |
| I_{TSM} | non-repetitive peak on-state current | full sine wave; $T_{\text{j}} = 25\text{ °C}$ prior to surge; see Figure 2 and 3 | | | |
| | | $t = 20\text{ ms}$ | - | 9 | A |
| | | $t = 16.7\text{ ms}$ | - | 10 | A |
| I^2t | I^2t for fusing | $t_{\text{p}} = 10\text{ ms}$ | - | 0.32 | A^2s |
| di_{T}/dt | rate of rise of on-state current | $I_{\text{TM}} = 1\text{ A}$; $I_{\text{G}} = 20\text{ mA}$; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$ | | | |
| | | T2+ G+ | - | 50 | $\text{A}/\mu\text{s}$ |
| | | T2+ G- | - | 50 | $\text{A}/\mu\text{s}$ |
| | | T2- G- | - | 50 | $\text{A}/\mu\text{s}$ |
| | | T2- G+ | - | 10 | $\text{A}/\mu\text{s}$ |
| I_{GM} | peak gate current | | - | 1 | A |
| P_{GM} | peak gate power | | - | 5 | W |
| $P_{\text{G(AV)}}$ | average gate power | over any 20 ms period | - | 0.1 | W |
| T_{stg} | storage temperature | | -40 | +150 | $^{\circ}\text{C}$ |
| T_{j} | junction temperature | | - | 125 | $^{\circ}\text{C}$ |



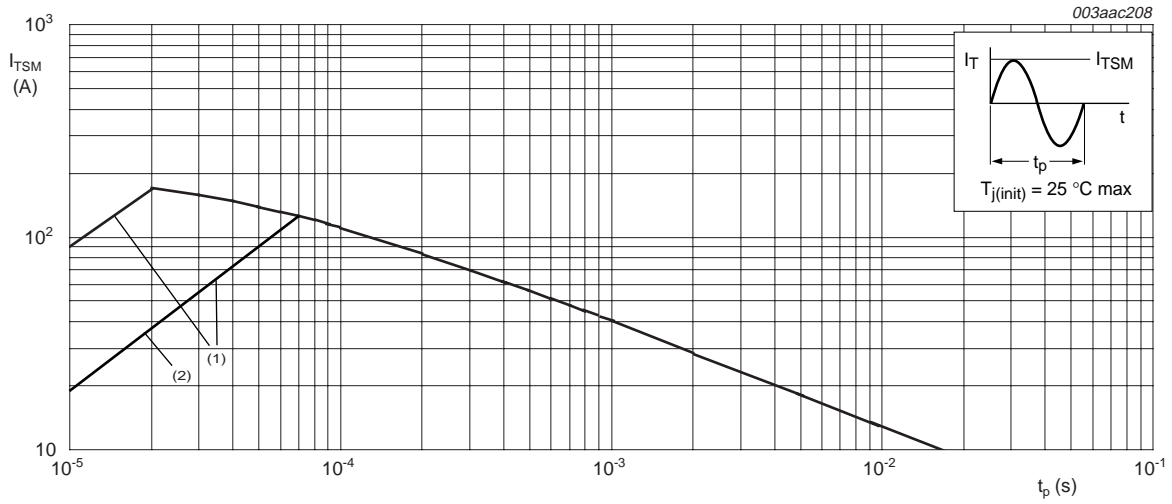
α = conduction angle

Fig 1. Total power dissipation as a function of RMS on-state current; maximum values



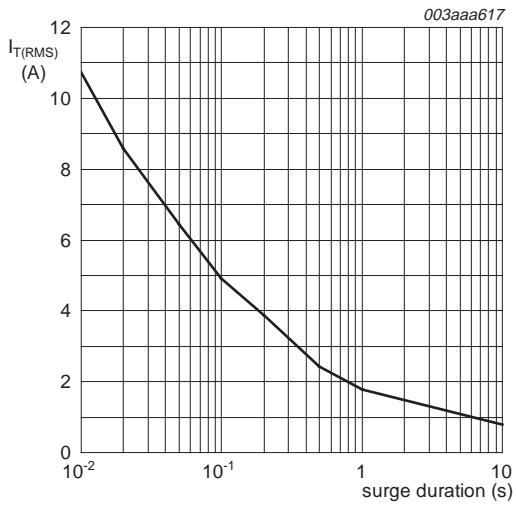
f = 50 Hz

Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



- $t_p \leq 20 \text{ ms}$
- (1) dI_T/dt limit
 - (2) T2- G+ quadrant limit

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values



$f = 50 \text{ Hz}$
 $T_{\text{lead}} = 55 \text{ }^\circ\text{C}$

Fig 4. RMS on-state current as a function of surge duration; maximum values

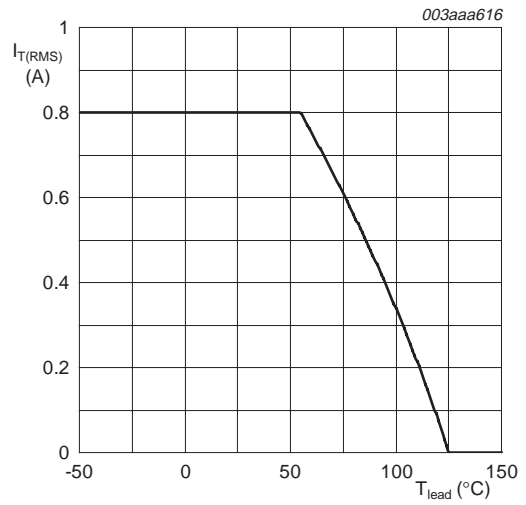
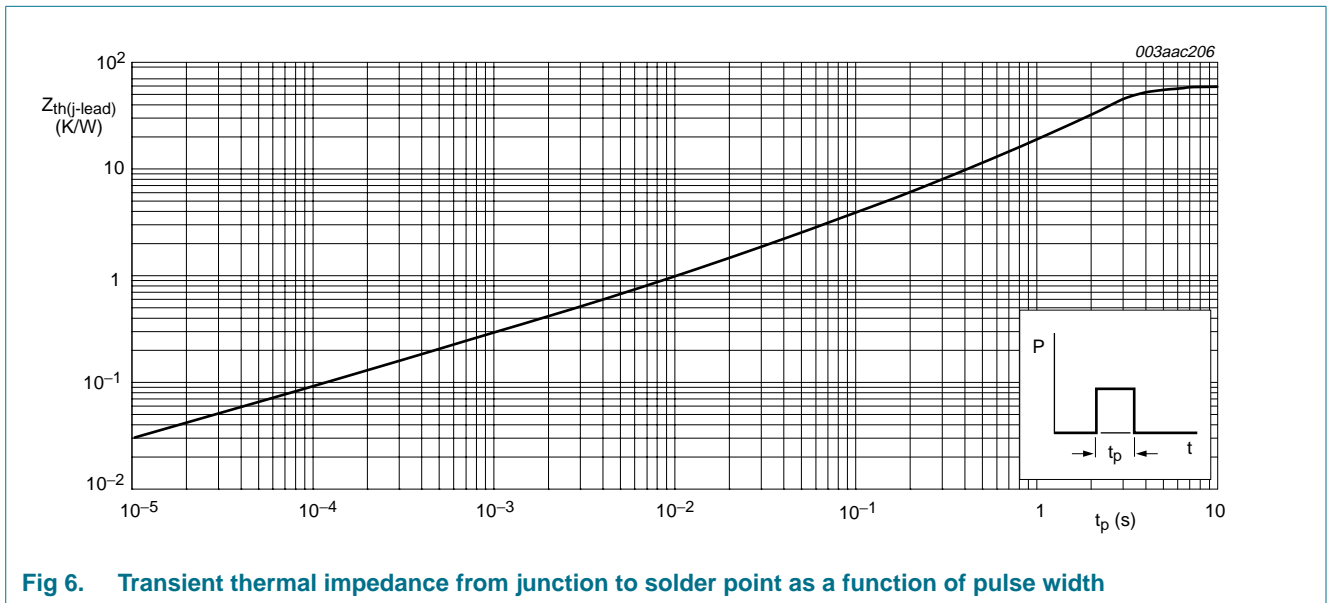


Fig 5. RMS on-state current as a function of lead temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------|---|---|-----|-----|-----|------|
| $R_{th(j-lead)}$ | thermal resistance from junction to lead | full cycle | - | - | 60 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | full cycle; printed-circuit board mounted; lead length 4 mm; see Figure 6 | - | 150 | - | K/W |



6. Characteristics

Table 5. Characteristics
T_j = 25 °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|---------------------------------------|--|-----|------|-----|------|
| Static characteristics | | | | | | |
| I _{GT} | gate trigger current | V _D = 12 V; I _T = 0.1 A; see Figure 8 | | | | |
| | | T2+ G+ | - | 1 | 5 | mA |
| | | T2+ G- | - | 2 | 5 | mA |
| | | T2- G- | - | 2 | 5 | mA |
| | | T2- G+ | - | 4 | 7 | mA |
| I _L | latching current | V _D = 12 V; I _G = 0.1 A; see Figure 10 | | | | |
| | | T2+ G+ | - | 1 | 10 | mA |
| | | T2+ G- | - | 5 | 10 | mA |
| | | T2- G- | - | 1 | 10 | mA |
| | | T2- G+ | - | 2 | 10 | mA |
| I _H | holding current | V _D = 12 V; I _G = 0.1 A; see Figure 11 | - | 1 | 10 | mA |
| V _T | on-state voltage | I _T = 0.85 A; see Figure 9 | - | 1.35 | 1.6 | V |
| V _{GT} | gate trigger voltage | V _D = 12 V; I _T = 0.1 A; see Figure 7 | - | 0.9 | 2 | V |
| | | V _D = V _{DRM} ; I _T = 0.1 A; T _j = 110 °C | 0.1 | 0.7 | - | V |
| I _D | off-state current | V _D = V _{DRM(max)} ; T _j = 125 °C | - | 0.1 | 0.5 | mA |
| Dynamic characteristics | | | | | | |
| dV _D /dt | rate of rise of off-state voltage | V _{DM} = 0.67 × V _{DRM(max)} ; T _j = 110 °C; exponential waveform; gate open circuit | 30 | 45 | - | V/μs |
| dV _{com} /dt | rate of change of commutating voltage | V _{DM} = V _{DRM(max)} ; T _j = 50 °C; I _{TM} = 0.84 A; dI _{com} /dt = 0.3 A/ms | - | 5 | - | V/μs |
| t _{gt} | gate-controlled turn-on time | I _{TM} = 1 A; V _D = V _{DRM(max)} ; I _G = 25 mA; dI _G /dt = 5 A/μs | - | 2 | - | μs |

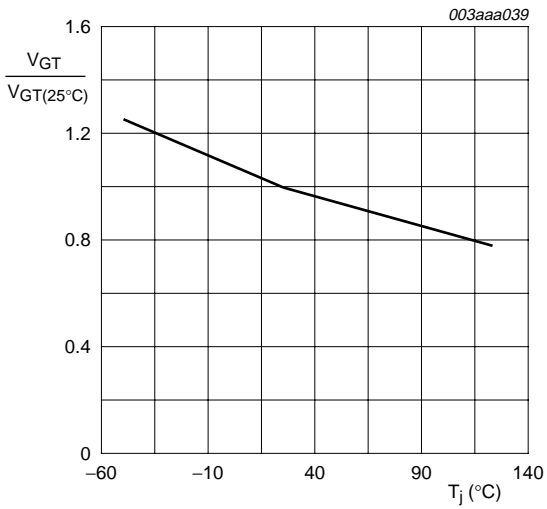
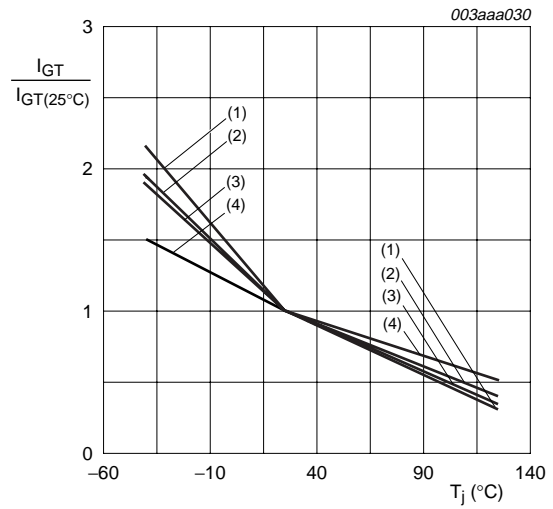
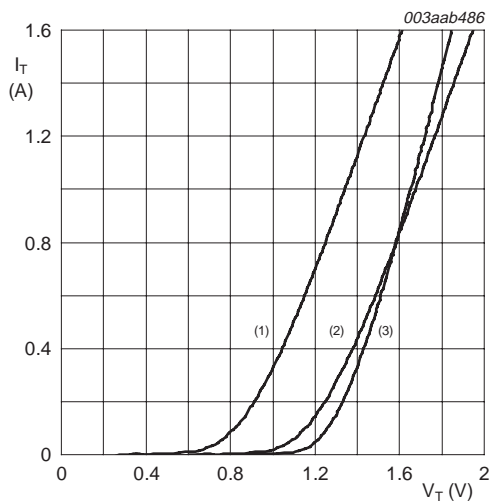


Fig 7. Normalized gate trigger voltage as a function of junction temperature



- (1) T2+ G+
- (2) T2- G+
- (3) T2- G-
- (4) T2+ G-

Fig 8. Normalized gate trigger current as a function of junction temperature



- $V_o = 1.171 \text{ V}$
 $R_s = 0.5125 \Omega$
- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
 - (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
 - (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig 9. On-state current as a function of on-state voltage

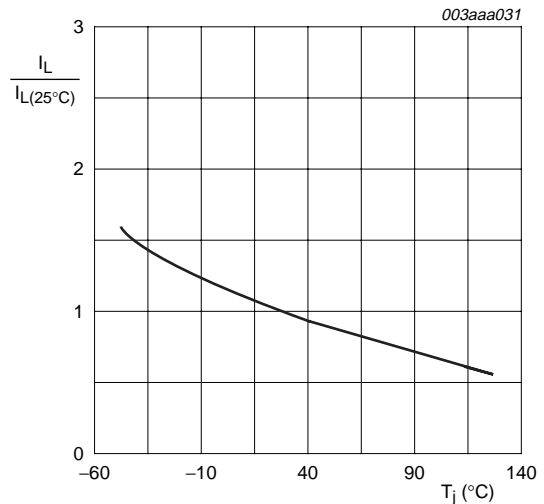


Fig 10. Normalized latching current as a function of junction temperature

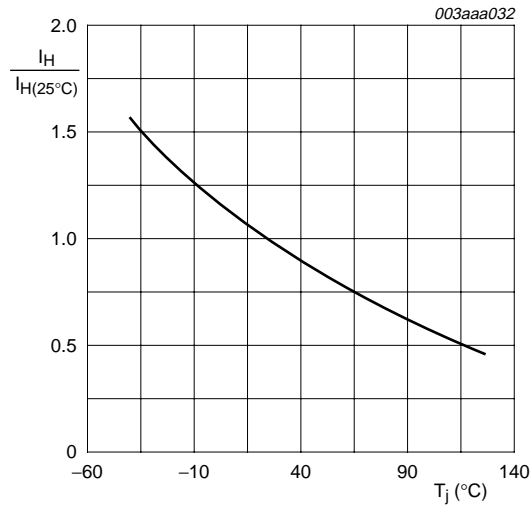


Fig 11. Normalized holding current as a function of junction temperature

7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

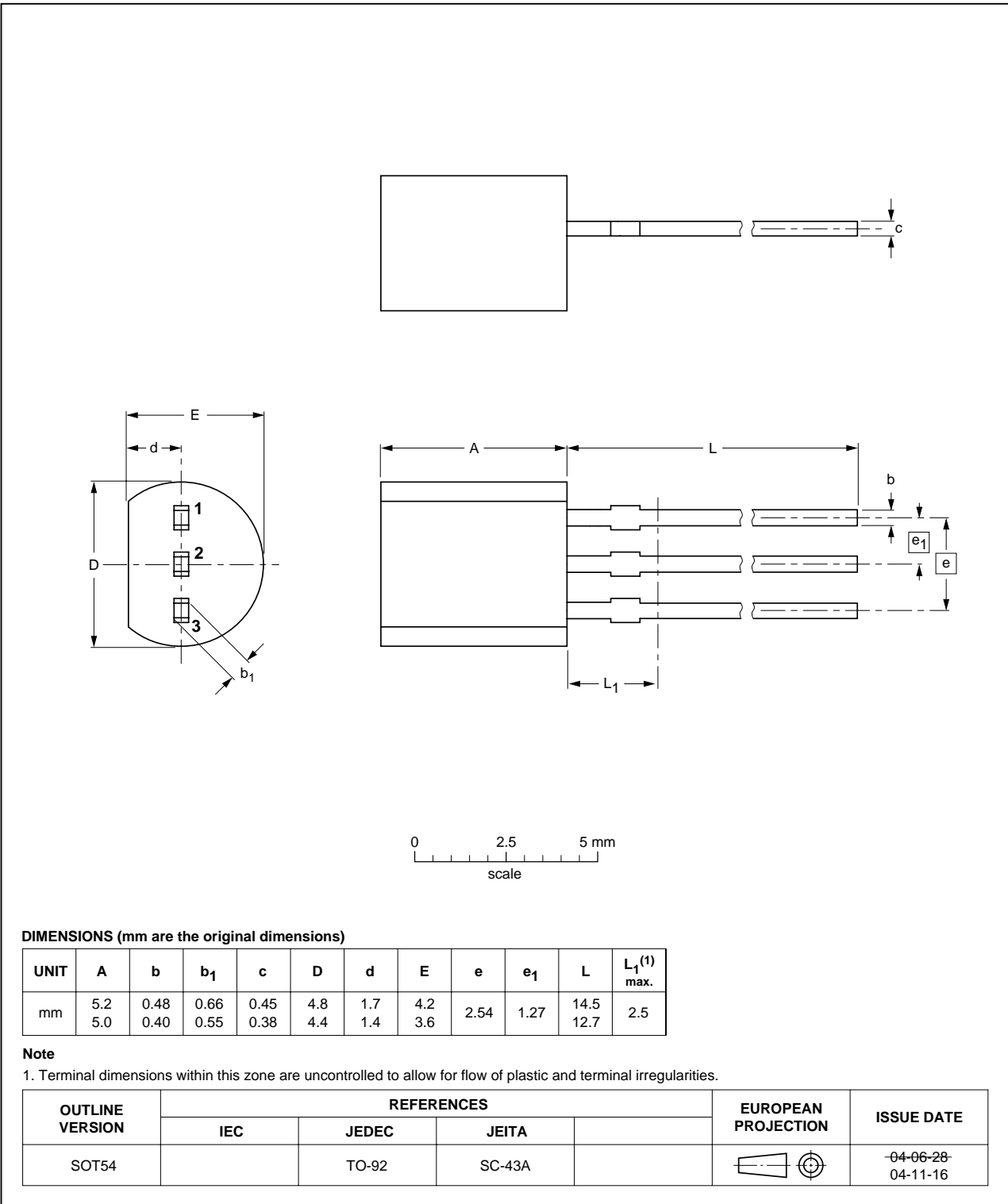


Fig 12. Package outline SOT54 (TO-92)

8. Revision history

Table 6. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| BT1308_SER_D_1 | 20080226 | Product data sheet | - | - |

9. Legal information

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| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

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11. Contents

| | | |
|-----------|--------------------------------------|-----------|
| 1 | Product profile | 1 |
| 1.1 | General description | 1 |
| 1.2 | Features | 1 |
| 1.3 | Applications | 1 |
| 1.4 | Quick reference data | 1 |
| 2 | Pinning information | 1 |
| 3 | Ordering information | 2 |
| 4 | Limiting values | 2 |
| 5 | Thermal characteristics | 5 |
| 6 | Characteristics | 6 |
| 7 | Package outline | 9 |
| 8 | Revision history | 10 |
| 9 | Legal information | 11 |
| 9.1 | Data sheet status | 11 |
| 9.2 | Definitions | 11 |
| 9.3 | Disclaimers | 11 |
| 9.4 | Trademarks | 11 |
| 10 | Contact information | 11 |
| 11 | Contents | 12 |



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